

TK12 Phase Control Thyristor

DS4252-5.0 July 2001

Replaces January 2000 version, DS4252-4.0

FEATURES

■ High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control
- Welding
- Battery Chargers

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} V _{RRM} V	Conditions
TK12 20 M or K TK12 18 M or K TK12 16 M or K TK12 14 M or K	2000 1800 1600 1400	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table, then:-

Add K to type number for 1/2" 20 UNF thread, e.g. TK12 18K.

or

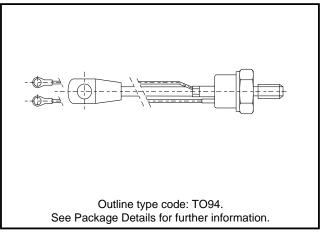
Add M to type number for M12 thread, e.g. TK12 14M.

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

KEY PARAMETERS

V _{drm}	2000V
Ι _{τ(AV)}	75A
I _{TSM}	1400A
dVdt*	200V/ μs
dl/dt	500Α/ μs

*Higher dV/dt selections available







CURRENT RATINGS

T_{case} = 60°C unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
I _{T(AV)}	Mean on-state current	Half wave resistive load	104	А
I _{T(RMS)}	RMS value	-	163	A
Ι _τ	Continuous (direct) on-state current	-	139	A

T_{case} = 80°C unless stated otherwise.

Symbol	Parameter	Conditions	Max.	Units
I _{T(AV)}	Mean on-state current	Half wave resistive load	75	А
I _{T(RMS)}	RMS value	-	120	A
Ι _τ	Continuous (direct) on-state current	-	100	А

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	1.12	kA
l²t	I ² t for fusing	V _R = 50% V _{RRM} - 1/4 sine	6.2 x 10 ³	A ² s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	1.4	kA
l²t	I ² t for fusing	V _R = 0	9.8 x 10 ³	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	dc	-	0.24	°C/W
R _{th(c-h)}	Thermal resistance - case to heatsink	Mounting torque 15.0Nm with mounting compound	-	0.08	°C/W
		On-state (conducting)	-	125	ů
T _{vj}	Virtual junction temperature	Reverse (blocking)	-	125	°C
T _{stg}	Storage temperature range		-40	150	°C
-	Mounting torque		12.0	15.0	Nm



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions		Min.	Max.	Units
V _{TM}	Maximum on-state voltage	At 150A peak, T _{case} = 25°C		-	2.0	V
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	10	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 60% $V_{DRM} T_j = 125^{\circ}C$, Gate open circuit		-	200	V/µs
-11/-14	dl/dt Rate of rise of on-state current Gate source 20V, 20 Ω t _r \leq 0.5 μ s, T _j = 125°C		Repetitive 50Hz	-	500	A/μs
ai/at		$t_r \le 0.5 \mu s, T_j = 125 C$	Non-repetitive	-	800	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.4	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	4.0	mΩ
t _{gd}	Delay time	$V_{_{D}} = 300V, I_{_{G}} = 1A, I_{_{T}} = 50A, dI/dt = 50A/\mu s, dI_{_{G}}/dt = 1A/\mu s, T_{_{J}} = 25^{\circ}C$		-	1.5	μs
I _L	Latching current	$T_{j} = 25^{\circ}C, V_{D} = 12V$		-	-	mA
I _H	Holding current	$T_{j} = 25^{\circ}C, V_{D} = 12V, I_{TM} = 1A$	\	-	50	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Тур.	Max.	Units
V _{GT}	Gate trigger voltage	$V_{\text{DRM}} = 12V, T_{\text{case}} = 25^{\circ}\text{C}, R_{\text{L}} = 6\Omega$	-	3.0	V
I _{GT}	Gate trigger current	$V_{\text{DRM}} = 12V, \ T_{\text{case}} = 25^{\circ}\text{C}, \ R_{\text{L}} = 6\Omega$	-	125	mA
V _{gd}	Gate non-trigger voltage	At $V_{DRM} T_{case} = 125^{\circ}C$, $R_{L} = 12\Omega$	-	0.2	V
V _{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	-	3.0	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V _{rgm}	Peak reverse gate voltage		-	5	V
I _{FGM}	Peak forward gate current	Anode positive with respect to cathode	-	4	A
P _{GM}	Peak gate power	-	-	16	w
$P_{G(AV)}$	Mean gate power		-	3	W



CURVES SINUSOIDAL CURRENT WAVEFORM 2000 Measured under pulse conditions T_j = 125°C 360° **RECTANGULAR CURRENT WAVEFORM** β 0 360° 8.0 0 4.0 12.0 Instantaneous on-state voltage V_T - (V) Fig.2 Maximum (limit) on-state characteristics 400 125 120 Maximum allowable case temperature, T_{C} (°C) 110 AVERAGE POWER DISSIPATION, P_{T(AV)} (W) 300 100 90 200 80 70 100 60 Q п g g 50 45 0 50 100 150 0 50 100 150 200 200 AVERAGE CURRENT, IT (AV) (A) AVERAGE CURRENT, $I_{T(AV)}$ (A) Fig.3 Maximum on-state power dissipation for sinusoidal Fig.4 Maximum allowable case temperature for sinusoidal current waveform current waveform

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40

10

5

3

1

0.1

0.01

gate voltage. V_G (V)

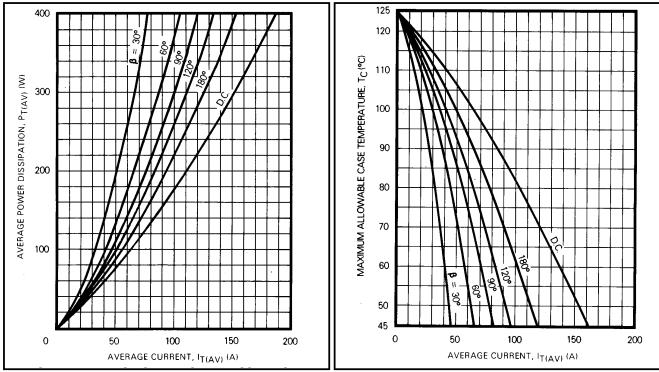
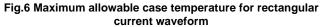


Fig.5 Maximum on-state power dissipation for rectangular current waveform



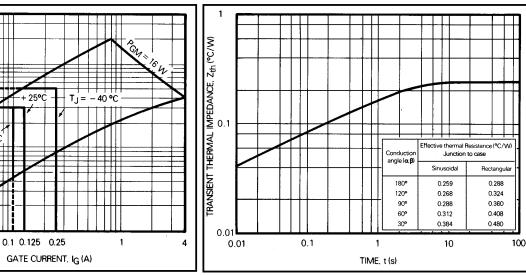
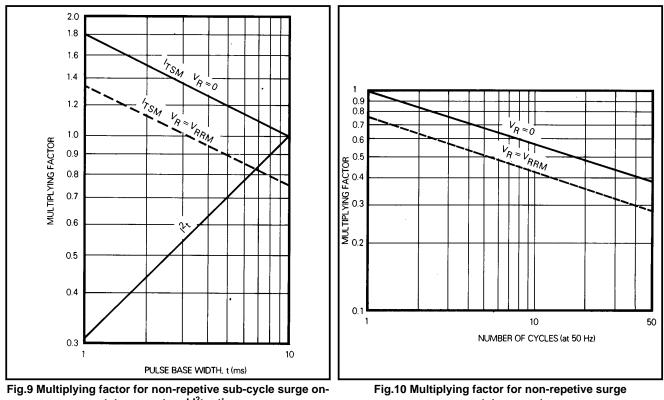


Fig.7 Gate trigger characteristics

Fig.8 Transient thermal impedance - junction to case

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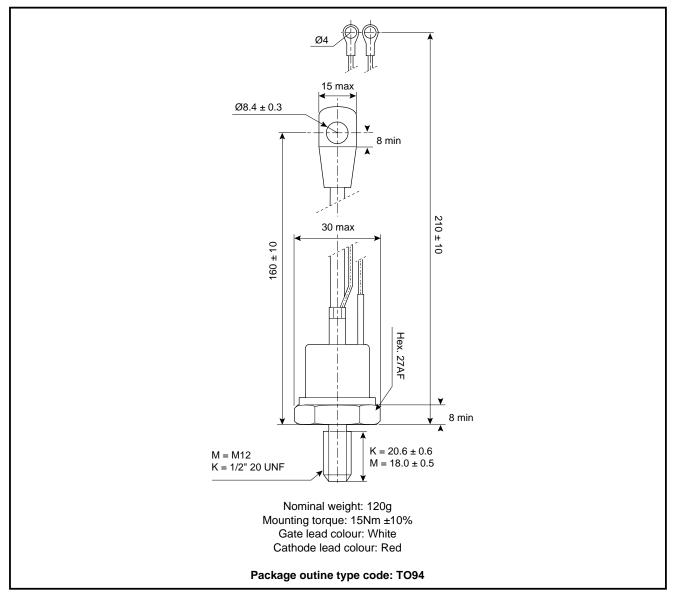
state current and I²t rating

on-state current



PACKAGE DETAILS

For further package information, please contact your nearest Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACS range includes a varied selection of pre-loaded clamps to suit all of our manufactured devices. Types available include cube clamps for single side cooling of 'T' 23mm and 'E' 30mm discs, and bar clamps right up to 83kN for our 'Z' 100mm thyristors and diodes.

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or customer service office.



Datasheet Annotations:

Dynex Semiconductor annotate datasheets in the top right hard corner of the front page, to indicate product status. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification. No actual design work on the product has been started.

Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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